

1SS119

Silicon Epitaxial Planar Diode for High Speed Switching

HITACHI

ADE-208-180A (Z)

Rev. 1

Aug. 1995

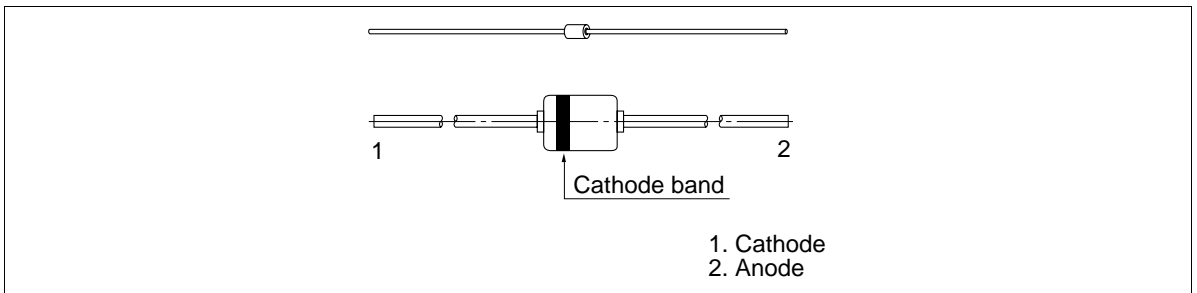
Features

- Low capacitance. ($C = 3.0\text{pF max}$)
- Short reverse recovery time. ($t_{rr} = 3.5\text{ns max}$)
- Small glass package (MHD) enables easy mounting and high reliability.

Ordering Information

| Type No. | Cathode band | Package Code |
|----------|--------------|--------------|
| 1SS119 | Light Blue | MHD |

Outline



Absolute Maximum Ratings (Ta = 25°C)

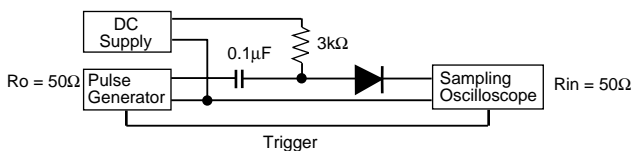
| Item | Symbol | Value | Unit |
|---|-------------|-------------|------|
| Peak reverse voltage | V_{RM} | 35 | V |
| Reverse voltage | V_R | 30 | V |
| Peak forward current | I_{FM} | 450 | mA |
| Non-Repetitive peak forward surge current | I_{FSM}^* | 1 | A |
| Average forward current | I_O | 150 | mA |
| Power dissipation | Pd | 250 | mW |
| Junction temperature | Tj | 175 | °C |
| Storage temperature | Tstg | -65 to +175 | °C |

Note: Within 1s forward surge current.

Electrical Characteristics (Ta = 25°C)

| Item | Symbol | Min | Typ | Max | Unit | Test Condition |
|-----------------------|------------|-----|-----|-----|---------------|--|
| Forward voltage | V_F | — | — | 0.8 | V | $I_F = 10\text{mA}$ |
| Reverse current | I_R | — | — | 0.1 | μA | $V_R = 30\text{V}$ |
| Capacitance | C | — | — | 3.0 | pF | $V_R = 1\text{V}, f = 1\text{MHz}$ |
| Reverse recovery time | t_{rr}^* | — | — | 3.5 | ns | $I_F = 10\text{mA}, V_R = 6\text{V}, R_L = 50\Omega$ |

Note: Reverse recovery time test circuit



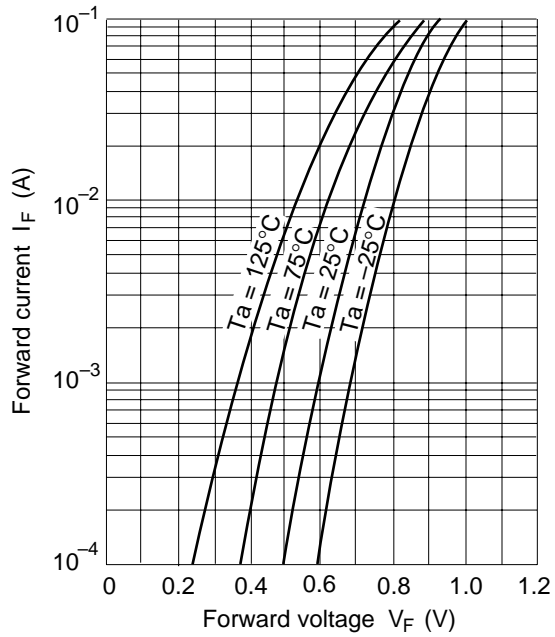


Fig.1 Forward current Vs. Forward voltage

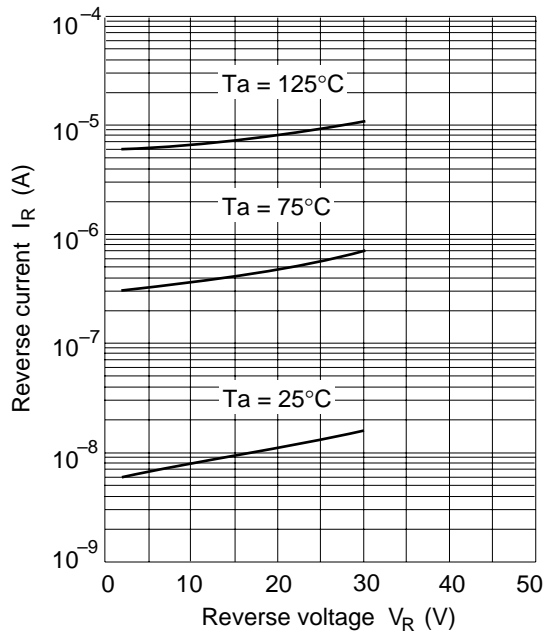


Fig.2 Reverse current Vs. Reverse voltage

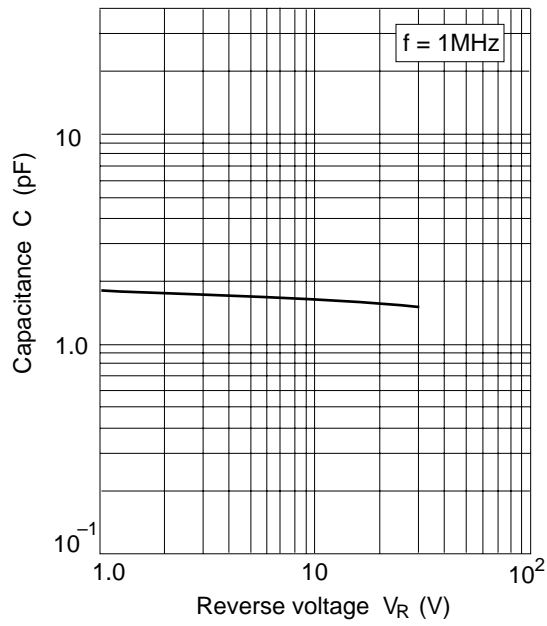
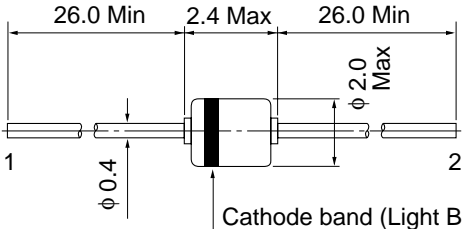


Fig.3 Capacitance Vs. Reverse voltage

Package Dimensions

Unit: mm



- 1 Cathode
- 2 Anode

| | |
|--------------|-------|
| HITACHI Code | MHD |
| JEDEC Code | DO-34 |
| EIAJ Code | — |
| Weight (g) | 0.084 |

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HITACHI

Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL North America : <http://semiconductor.hitachi.com/>
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For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose, CA 95134
Tel: <1> (408) 433-1990
Fax: <1> (408) 433-0223

Hitachi Europe GmbH
Electronic components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia Ltd.
Taipei Branch Office
3F, Hung Kuo Building, No.167,
Tun-Hwa North Road, Taipei (105)
Tel: <886> (2) 2718-3666
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX

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